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## FODM217 Series

## Single Channel, DC Sensing Input, Phototransistor Optocoupler In Half-Pitch Mini-Flat 4-Pin Package

The FODM217 Series single channel, DC sensing input, optocoupler consists of one gallium arsenide (GaAs) infrared light emitting diode optically coupled to one phototransistor, in a compact, half-pitch, mini-flat, 4-pin package. The input-output isolation voltage, VISO, is rated at 3,750 VAC<sub>RMS</sub>.

#### Features

- Current Transfer Ratio Ranges from 80 to 600% at  $I_F = 5 \text{ mA}$ ,
  - $V_{CE} = 5 V, T_A = 25^{\circ}C$
  - FODM217A 80 to 160%
  - FODM217B 130 to 260%
  - FODM217C 200 to 400%
  - FODM217D 300 to 600%
- Safety and Regulatory Approvals:
  UL1577, 3750 VACRMS for 1 min
  DIN EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- Applicable to Infrared Ray Reflow, 260°C

### **Typical Applications**

- Primarily Suited for DC-DCConverters
- For Ground Loop Isolation, Signal to Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control



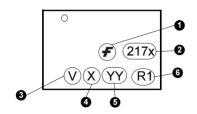
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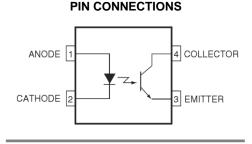


**SOP 4 PINS** 

#### MARKING DIAGRAM



- 1. F = Corporate Logo
- 2. 217x = Device Number
- 3. V = DIN EN/IEC60747-5-5 Option
- 4. X = One-Digit Year Code
- 5. YY = Digit Work Week
- 6. R1 = Assembly Package Code



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

 $\ensuremath{\textcircled{o}}$  Semiconductor Components Industries, LLC, 2016 January 2017 - Rev. P0

## SAFETY AND INSULATIONS RATING

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

| Parameter   | Characteristics        |       |
|---|------------------------|-------|
| Installation Classifications per DIN VDE 0110/1.89 Table 1, | < 150 V <sub>RMS</sub> | I–IV  |
| For Rated Mains Voltage                                     | < 300 V <sub>RMS</sub> | I–III |
| Climatic Classification                                     | 55/110/21              |       |
| Pollution Degree (DIN VDE 0110/1.89)                        | 2                      |       |
| Comparative Tracking Index                                  | 175                    |       |

| Symbol                | Parameter  | Value             | Unit              |
|-----------------------|--|-------------------|-------------------|
| V <sub>PR</sub>       | Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with t <sub>m</sub> = 10 s, Partial Discharge < 5 pC       | 904               | V <sub>peak</sub> |
|                       | Input-to-Output Test Voltage, Method B, V <sub>IORM</sub> x 1.875 = V <sub>PR</sub> , 100%<br>Production Test with $t_m = 1$ s, Partial Discharge < 5 pC | 1060              | V <sub>peak</sub> |
| V <sub>IORM</sub>     | Maximum Working Insulation Voltage   | 565               | V <sub>peak</sub> |
| V <sub>IOTM</sub>     | Highest Allowable Over-Voltage   | 4,000             | V <sub>peak</sub> |
|                       | External Creepage  | ≥ 5               | mm                |
|                       | External Clearance   | ≥ 5               | mm                |
| DTI                   | Distance Through Insulation (Insulation Thickness)   | ≥ 0.4             | mm                |
| Τ <sub>S</sub>        | Case Temperature (Note 1)  | 150               | °C                |
| I <sub>S,INPUT</sub>  | Input Current (Note 1)   | 200               | mA                |
| P <sub>S,OUTPUT</sub> | Output Power (Note 1)  | 300               | mW                |
| R <sub>IO</sub>       | Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V (Note 1)   | > 10 <sup>9</sup> | Ω                 |

1. Safety limit values – maximum values allowed in the event of a failure.

## ABSOLUTE MAXIMUM RATINGS (Note 2)

| Symbol                  | Parameter  | Value          | Units |
|-------------------------|--|----------------|-------|
| T <sub>STG</sub>        | Storage Temperature  | -55 to +150    | °C    |
| T <sub>OPR</sub>        | Operating Temperature  | -55 to +110    | °C    |
| TJ                      | Junction Temperature   | -55 to +125    | °C    |
| T <sub>SOL</sub>        | Lead Solder Temperature<br>(Refer to Reflow Temperature Profile) | 260 for 10 sec | °C    |
| Emitter                 |  |                |       |
| I <sub>F(average)</sub> | Continuous Forward Current                                       | 50             | mA    |
| I <sub>F(peak)</sub>    | Peak Forward Current (1 µs pulse, 300 pps)                       | 1              | A     |
| V <sub>R</sub>          | Reverse Input Voltage  | 6              | V     |
| PDLED                   | Power Dissipation (Note 3)                                       | 70             | mW    |
| Detector                |  |                |       |
| I <sub>C(average)</sub> | Continuous Collector Current                                     | 50             | mA    |
| V <sub>CEO</sub>        | Collector-Emitter Voltage  | 80             | V     |
| V <sub>ECO</sub>        | Emitter-Collector Voltage  | 7              | V     |
| PDC                     | Collector Power Dissipation (Note 3)                             | 150            | mW    |

2. Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 3. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside

these ratings.

## **ELECTRICAL CHARACTERISTICS**

 $T_A = 25^{\circ}C$  unless otherwise specified

| Symbol            | Parameter                              | Conditions   | Min. | Тур. | Max. | Units |
|-------------------|--|--|------|------|------|-------|
| Emitter           |  |  |      |      |      |       |
| V <sub>F</sub>    | Forward Voltage                        | I <sub>F</sub> = 20 mA                               |      | 1.2  | 1.4  | V     |
| I <sub>R</sub>    | Reverse Current                        | V <sub>R</sub> = 4 V                                 |      |      | 10   | μΑ    |
| CT                | Terminal Capacitance                   | V = 0 V, f = 1 kHz                                   |      | 30   | 250  | pF    |
| Detector          |  |  |      |      | •    |       |
| BV <sub>CEO</sub> | Collector-Emitter Breakdown<br>Voltage | $I_{C} = 0.1 \text{ mA}, I_{F} = 0 \text{ mA}$       | 80   |      |      | V     |
| BV <sub>ECO</sub> | Emitter-Collector Breakdown<br>Voltage | $I_{E} = 10 \ \mu A, \ I_{F} = 0 \ m A$              | 7    |      |      | V     |
| I <sub>CEO</sub>  | Collector Dark Current                 | $V_{CE} = 50 \text{ V}, ^{I}\text{F} = 0 \text{ mA}$ |      |      | 100  | nA    |

#### **TRANSFER CHARACTERISTICS** TA=25°C unless otherwise specified

| Symbol               | Parameter                                     | Device   | Conditions                                     | Min. | Тур. | Max. | Units |
|----------------------|---|----------|--|------|------|------|-------|
|                      |   | FODM217A |  | 80   |      | 160  | 0/    |
| CTR <sub>CE</sub>    | Current Transfer Ratio<br>(collector-emitter) | FODM217B | <sup>I</sup> F = 5 mA, <sup>V</sup> CE = 5 V   | 130  |      | 260  | %     |
| 0L                   |   | FODM217C |  | 200  |      | 400  |       |
|                      |   | FODM217D |  | 300  |      | 600  |       |
| Ι <sub>C</sub>       | Collector Current                             | All      | I <sub>F</sub> = 5 mA, <sup>V</sup> CE = 5 V   | 4    |      | 30   | mA    |
| $CTR_{(SAT)}$        | Saturated Current Transfer<br>Ratio           | All      | <sup>I</sup> F = 8 mA, <sup>V</sup> CE = 0.4 V |      | 60   |      | %     |
| I <sub>C(SAT)</sub>  | Collector Current                             | All      | I <sub>F</sub> = 8 mA, <sup>V</sup> CE = 0.4 V |      | 4.8  |      | mA    |
| V <sub>CE(SAT)</sub> | Collector-Emitter<br>Saturation Voltage       | All      | <sup>I</sup> F = 8 mA, <sup>I</sup> C = 2.4 mA |      |      | 0.4  | V     |

## SWITCHING CHARACTERISTICS

## $T_A=25^{\circ}C$ unless otherwise specified

| Symbol           | Parameter                   | Conditions   | Min. | Тур. | Max. | Units |
|------------------|-----------------------------|--|------|------|------|-------|
| <sup>t</sup> ON  | Turn On Time                | $I_{C} = 2 \text{ mA}, V_{CE} = 10 \text{ V},$<br>$R_{L} = 100 \Omega$   |      | 3    |      | μs    |
| <sup>t</sup> OFF | Turn Off Time               | $I_C = 2 \text{ mA}, V_{CE} = 10 \text{ V},$<br>$R_L = 100 \Omega$       |      | 3    |      | μs    |
| t <sub>R</sub>   | Output Rise Time (10% -90%) | $I_{C} = 2 \text{ mA}, V_{CE} = 10 \text{ V},$<br>R <sub>L</sub> = 100 Ω |      | 2    |      | μs    |
| t <sub>F</sub>   | Output Fall Time (90% -10%) | $I_{C} = 2 \text{ mA}, V_{CE} = 10 \text{ V},$<br>$R_{L} = 100 \Omega$   |      | 3    |      | μs    |

## **ISOLATION CHARACTERISTICS**

| Symbol           | Parameter                      | Conditions  | Min.                 | Тур. | Max. | Units              |
|------------------|--------------------------------|---|----------------------|------|------|--------------------|
| V <sub>ISO</sub> | Input-Output Isolation Voltage | Freq = 60 Hz, t = 1.0 min,<br>I <sub>I-O</sub> ≤ 10 μA (Note 4,5) | 3,750                |      |      | VAC <sub>RMS</sub> |
| R <sub>ISO</sub> | Isolation Resistance           | V <sub>I-O</sub> = 500 V (Note 4)                                 | 5 x 10 <sup>10</sup> |      |      | Ω                  |
| C <sub>ISO</sub> | Isolation Capacitance          | Frequency = 1 MHz   |                      | 0.6  | 1.0  | pF                 |

4. Device is considered a two terminal device: Pin 1 and 2 are shorted together and Pins 3 and 4 are shorted together. 5. 3,750 VAC<sub>RMS</sub> for 1 minute duration is equivalent to 4,500 VAC<sub>RMS</sub> for 1 second duration.

## **TYPICAL CHARACTERISTICS**

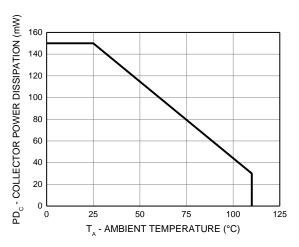


Figure 1. Collector Power Dissipation vs. Ambient Temperature

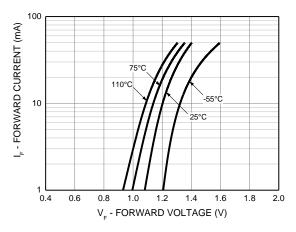


Figure 3. Forward Current vs. Forward Voltage

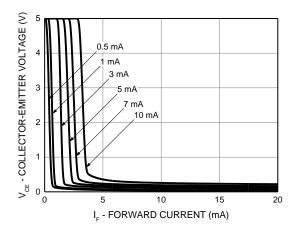


Figure 5. Collector Emitter Voltage vs. Forward Current

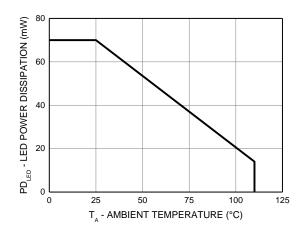


Figure 2. LED Power Dissipation vs. Ambient Temperature

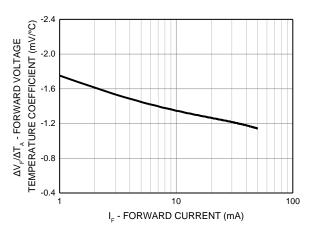


Figure 4. Forward Voltage Temperature Coefficient vs. Forward Current

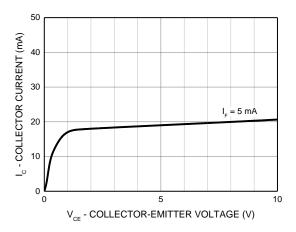


Figure 6. Collector Current vs. Collector-Emitter Voltage

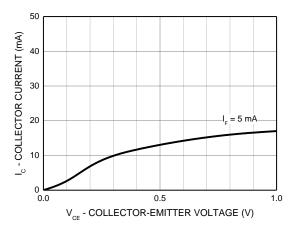


Figure 7. Collector Current vs. Small Collector-Emittter Voltage

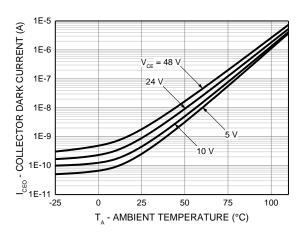


Figure 9. Collector Dark Current vs. Ambient Temperature

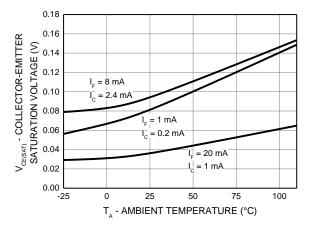


Figure 11. Collector-Emitter Saturation vs. Ambient Temperature

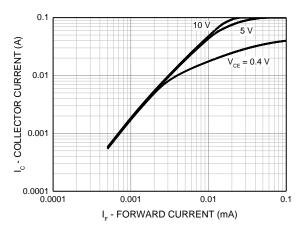


Figure 8. Collector Current vs. Forward Current

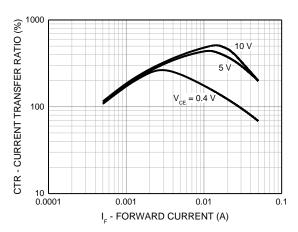


Figure 10. Current Transfer Ratio vs. Forward Current

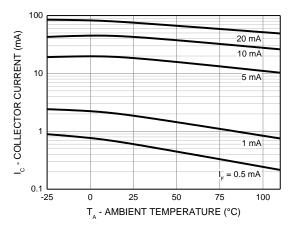


Figure 12. Collector Current vs. Ambient Temperature

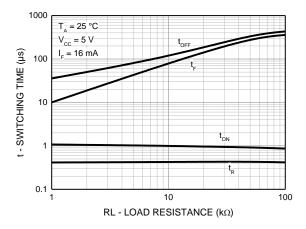


Figure 13. Switching Time vs. Load Resistance

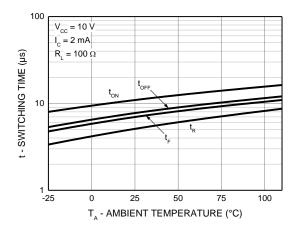


Figure 14. Switching Time vs. Ambient Temperature



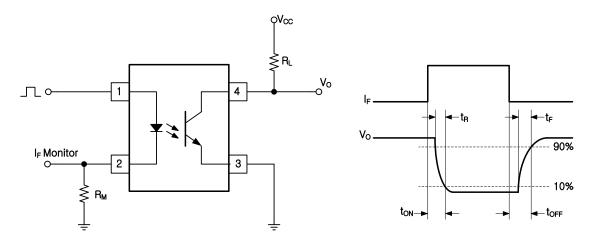
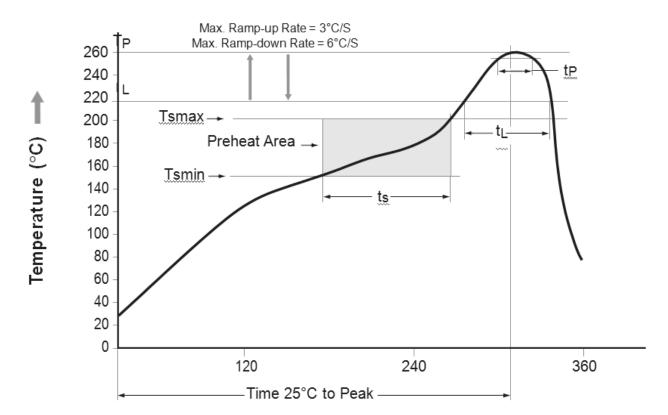


Figure 15. Test Circuit for Switching Time

## **REFLOW PROFILE**



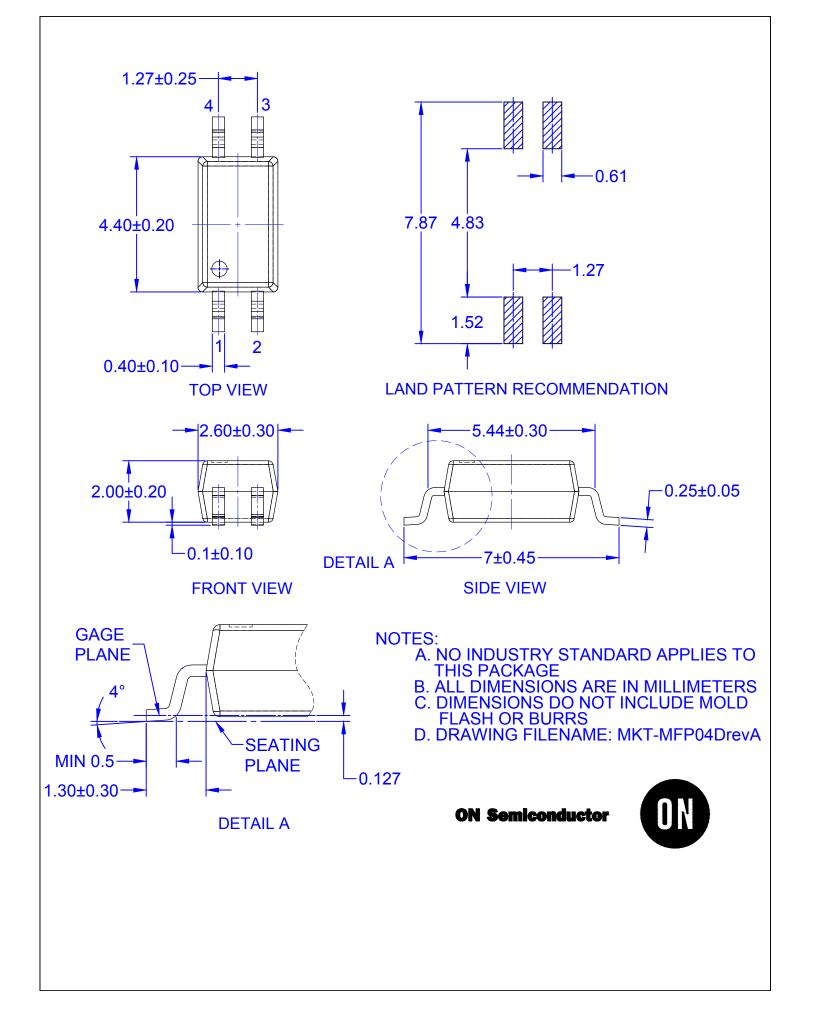
| Profile Freature                                   | Pb-Free Assembly Profile |
|--|--------------------------|
| Temperature Min. (Tsmin)                           | 150°C                    |
| Temperature Max. (Tsmax)                           | 200°C                    |
| Time (t <sub>S</sub> ) from (Tsmin to Tsmax)       | 60–120 seconds           |
| Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )   | 3°C/second max.          |
| Liquidous Temperature (TL)                         | 217°C                    |
| Time ( $t_L$ ) Maintained Above ( $T_L$ )          | 60–150 seconds           |
| Peak Body Package Temperature                      | 260°C +0°C / –5°C        |
| Time (t <sub>P</sub> ) within 5°C of 260°C         | 30 seconds               |
| Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> ) | 6°C/second max.          |
| Time 25°C to Peak Temperature                      | 8 minutes max.           |

Figure 36. Reflow Profile

## **ORDERING INFORMATION (Note 6)**

| Part Number | Package  | Packing Method             |
|-------------|--|----------------------------|
| FODM217A    | SOP 4-Pin  | Tube (100 units)           |
| FODM217AR2  | SOP 4-Pin  | Tape and Reel (3000 units) |
| FODM217AV   | SOP 4-Pin, DIN EN/IEC60747-5-5 Option (pending approval) | Tube (100 units)           |
| FODM217AR2V | SOP 4-Pin, DIN EN/IEC60747-5-5 Option (pending approval) | Tape and Reel (3000 units) |

6. The product orderable part number system listed in this table also applies to the FODM217B, FODM217C, and FODM217D products.



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